**Product data sheet** 

# 1. General description

Hyperfast power diode in a SOD59 (2-lead TO-220AC) plastic package.

## 2. Features and benefits

- · Extremely fast switching
- Low reverse recovery current
- · Low thermal resistance
- · Reduces switching losses in associated MOSFET

# 3. Applications

- Continuous Current Mode (CCM) Power
- Half-bridge or full-bridge switched-mode
- · Half-bridge lighting ballasts

## 4. Quick reference data

### Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage		600				V
$I_{F(AV)}$	average forward current	$δ = 0.5$ ; square-wave pulse; $T_{mb} \le 98$ °C; Fig. 1; Fig. 2	15		А		
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; $t_p$ = 25 μs; $T_{mb}$ ≤ 98 °C; square-wave pulse	30			А	
I <sub>FSM</sub> non-repetitive peak		$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	200			Α	
	forward current	$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	220			Α	
Symbol	Parameter	Conditions	Min Typ Max		Max	Unit	
Static ch	aracteristics		,				
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 15 A; T <sub>j</sub> = 150 °C; <u>Fig. 3</u>	- 1.4 2		V		
Dynamic	characteristics	'					
t <sub>rr</sub>	reverse recovery time	$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 4$		-	19	-	ns

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# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	
2	А	anode	7 7 9	K — A 001aaa020
mb	mb	mounting base; cathode	1 2 TO-220AC (SOD59)	001aaa020

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
BYC15-600	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59		

# 7. Marking

## Table 4. Marking codes

Type number	Marking codes
BYC15-600	BYC15-600

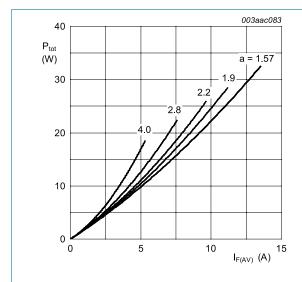
Hyperfast power diode

# 8. Limiting values

### **Table 5. Limiting values**

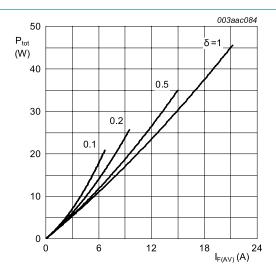
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		600	V
$V_{\text{RWM}}$	crest working reverse voltage		600	V
$V_R$	reverse voltage	T <sub>mb</sub> ≤ 100 °C; DC	500	V
$I_{F(AV)}$	average forward current	$δ = 0.5$ ; square-wave pulse; $T_{mb} \le 98$ °C; Fig. 1; Fig. 2	15	А
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 98 °C; square-wave pulse	30	А
I <sub>FSM</sub>	non-repetitive peak	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	200	А
	forward current	$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	220	Α
T <sub>stg</sub>	storage temperature		-40 to 150	°C
T <sub>j</sub>	junction temperature		150	°C



 $a = form factor = I_{F(RMS)} / I_{F(AV)}$ 

Fig. 1. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values



 $I_{\text{F(AV)}} = I_{\text{F(RMS)}} \times \sqrt{\delta}$ 

Fig. 2. Forward power dissipation as a function of average forward current; square waveform; maximum values

Hyperfast power diode

# 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

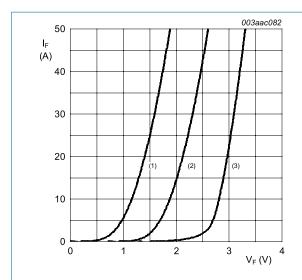
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	with heatsink compound	-	-	1.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W

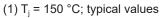
Hyperfast power diode

# 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30A; T <sub>j</sub> = 150 °C; <u>Fig. 3</u>	-	1.7	2.3	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 3</u>	-	1.9	2.9	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 150 °C; <u>Fig. 3</u>	-	1.4	2	V
I <sub>R</sub> reverse current		V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	12	200	μΑ
		V <sub>R</sub> = 500 V; T <sub>j</sub> = 100 °C	-	1.1	3	mA
Dynamic	characteristics					
t <sub>rr</sub>	reverse recovery time	$I_F = 15 \text{ A}$ ; $V_R = 400 \text{ V}$ ; $dI_F/dt = 500 \text{ A/}\mu\text{s}$ ; $T_i = 100 \text{ °C}$ ; Fig. 4	-	32	40	ns
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 4$	-	35	55	ns
		$I_F = 15 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 4$	-	19	-	ns
I <sub>RM</sub> peak reverse recovery current		$I_F = 15 \text{ A}$ ; $V_R = 400 \text{ V}$ ; $dI_F/dt = 500 \text{ A/}\mu\text{s}$ ; $T_j = 125 \text{ °C}$ ; Fig. 4	-	9.5	12	А
		$I_F = 15 \text{ A}$ ; $V_R = 400 \text{ V}$ ; $dI_F/dt = 50 \text{ A}/\mu\text{s}$ ; $T_j = 125 \text{ °C}$ ; Fig. 4	-	3	7.5	А
V <sub>FR</sub>	forward recovery voltage	$I_F = 15 \text{ A}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_i = 25 \text{ °C}; Fig. 5$	-	8	11	V





<sup>(2)</sup> T<sub>i</sub> = 150 °C; maximum values

Fig. 3. Forward current as a function of forward voltage

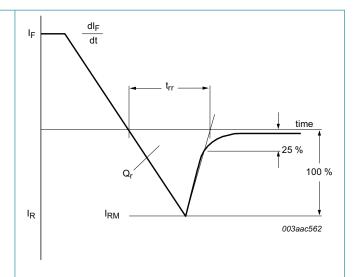
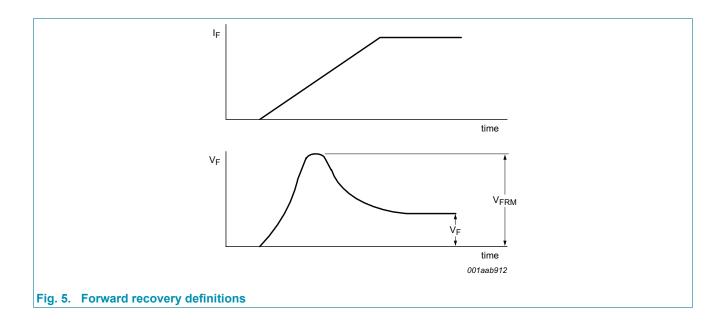


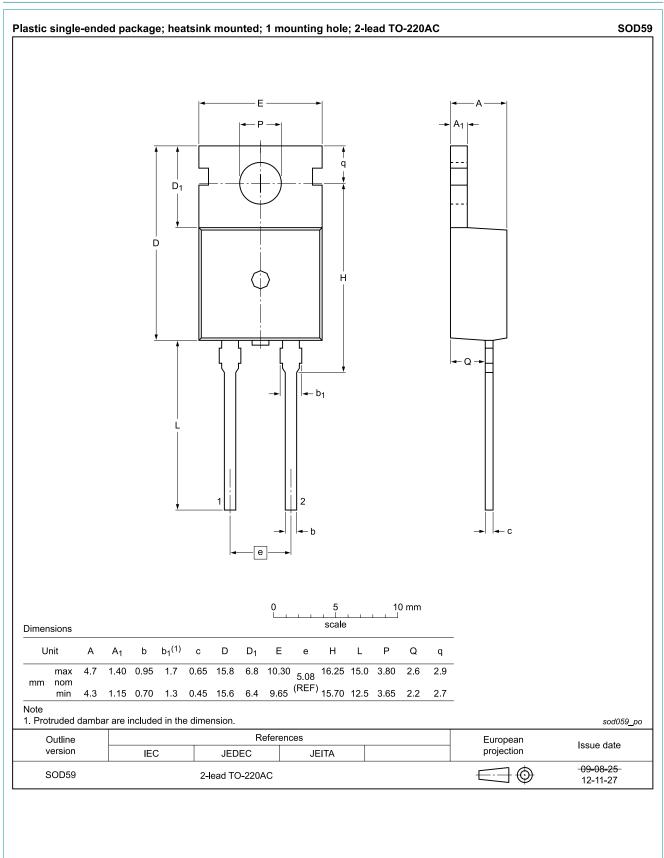
Fig. 4. Reverse recovery definitions; ramp recovery

<sup>(3)</sup>  $T_i = 25$  °C; maximum values

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# 11. Package outline



Hyperfast power diode

# 12. Revision history

### **Table 8. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BYC15-600 v.3	20180224	Product data sheet	-	BYC15-600 v.2	
Modifications: Change from NXP version to WeEn version					
BYC15-600 v.2	20100729	Product data sheet	-	BYC15-600 v.1	
Modifications: Various changes to content.					
BYC15-600 v.1	20071129	Product data sheet	-	-	

### Hyperfast power diode

## 13. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Date of release: 24 February 2018

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